

TO-92 Plastic-Encapsulate Transistors

2SC1008 TRANSISTOR (NPN)

FEATURES

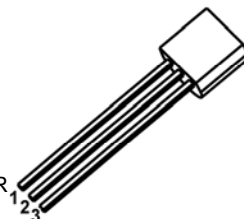
- General Purpose Switching and Amplification

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current	700	mA
P_C	Collector Power Dissipation	800	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	156	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

TO - 92

1. EMITTER
2. BASE
3. COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}, I_E = 0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.01\text{mA}, I_C = 0$	8			V
Collector cut-off current	I_{CBO}	$V_{CB} = 60\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 2\text{V}, I_C = 50\text{mA}$	40		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1.1	V
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_C = 0, f = 1\text{MHz}$		8		pF
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$	30			MHz

CLASSIFICATION OF h_{FE}

RANK	R	O	Y	G
RANGE	40-80	70-140	120-240	200-400